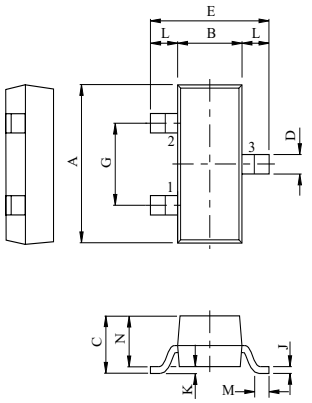
2N5551SC

EPITAXIAL PLANAR NPN TRANSISTOR

GENERAL PURPOSE APPLICATION.
HIGH VOLTAGE APPLICATION.

FEATURES

- High Collector Breakdwon Voltage
  : V_{CBO}=180V, V_{CEO}=160V
- Low Leakage Current.
  : I_{CBO}=50nA(Max.) V_{CB}=120V
- Low Saturation Voltage
  : $V_{CE(sat)}$=0.2V(Max.) I_C=50mA, I_B=5mA



DIM	MILLIMETERS
A	2.90±0.1
B	1.30+0.20/-0.15
C	1.30 MAX
D	0.40+0.15/-0.05
E	2.40+0.30/-0.20
G	1.90
J	0.10
K	0.00 ~ 0.10
L	0.55
M	0.20 MIN
N	1.00+0.20/-0.10

1. EMITTER
2. BASE
3. COLLECTOR

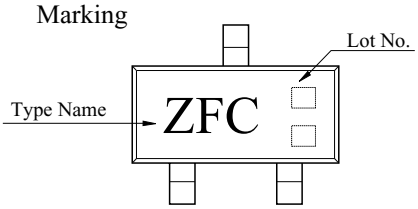
SOT-23(1)

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	180	V
Collector-Emitter Voltage	V_{CEO}	160	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	600	mA
Base Current	I_B	100	mA
Collector Power Dissipation	P_C *	350	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 150	℃

Note : * Package Mounted On 99.5% Alumina 10×8×0.6㎜)

Marking



ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=120V, I_E=0	-	-	50	nA
Emitter Cut-off Current	I_{EBO}	V_{EB}=4V, I_C=0	-	-	50	nA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=0.1mA, I_E=0	180	-	-	V
Collector-Emitter Breakdown Voltage *	$V_{(BR)CEO}$	I_C=1mA, I_B=0	160	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=0.1mA, I_C=0	5	-	-	V
DC Current Gain *	h_{FE}	V_{CE}=5V, I_C=10mA	150	-	250	
Collector-Emitter Saturation Voltage *	$V_{CE(sat)}$	I_C=50mA, I_B=5mA	-	-	0.5	V
Base-Emitter Saturation Voltage *	$V_{BE(sat)}$	I_C=50mA, I_B=5mA	-	-	1.0	V
Transition Frequency	f_T	V_{CE}=5V, I_C=10mA, f=30MHz	100	-	300	MHz

* Pulse Test : Pulse Width≦300 μS, Duty Cycle≦2%.